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Inventor(s)	Yue; Shiyu et al.

Metal oxide preclean for bottom-up gapfill in MEOL and BEOL

Abstract

A method of pre-cleaning in a semiconductor structure includes performing a plasma pre-treatment process to remove impurities from a surface of a semiconductor structure comprising a metal layer and a dielectric layer, performing a selective etch process to remove molybdenum oxide from a surface of the metal layer, the selective etch process comprising soaking the semiconductor structure in a precursor including molybdenum chloride (MoCl.sub.5, MoCl.sub.6) at a temperature of between 250° C. and 350° C., and performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure.

Inventors: Yue; Shiyu (Santa Clara, CA), Cen; Jiajie (Santa Clara, CA), Patel; Sahil Jaykumar (Sunnyvale, CA), Qi; Zhimin (Santa Clara, CA), Oh; Ju Hyun (San Jose, CA), Zhang; Aixi (Santa Clara, CA), Gao; Xingyao (Santa Jose, CA), Lei; Wei (Santa Clara, CA), Xu; Yi (San Jose, CA), Lei; Yu (Belmont, CA), Yang; Tsung-Han (San Jose, CA), Wang; Xiaodong (San Jose, CA), Xie; Xiangjin (Fremont, CA), Yang; Yixiong (San Jose, CA), Kashefi; Kevin (Dublin, CA), Wang; Rongjun (Dublin, CA)

Applicant: Applied Materials, Inc. (Santa Clara, CA)

Family ID: 1000008764418

Assignee: APPLIED MATERIALS, INC. (Santa Clara, CA)

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Primary Examiner: Deo; Duy Vu N

Attorney, Agent or Firm: Patterson + Sheridan, LLP

Background/Summary

BACKGROUND

Field

(1) Embodiments described herein generally relate to semiconductor device fabrication. More specifically, embodiments of the present disclosure relate to methods for pre-cleaning a surface of a semiconductor device to selectively remove metal oxides, and reduce chlorine or fluorine residues.

Description of the Related Art

(2) In fabrication of an integrated circuit, middle-end-of-line (MEOL) and back-end-of-line (BEOL) stages may include forming gate regions of transistors and local interconnect layers with molybdenum (Mo). Conventionally, a surface of a metal layer or a dielectric layer is pre-cleaned to remove metal oxides, such as molybdenum oxide (MoO.sub.x) and tungsten oxide (WO.sub.x), and reduce chlorine or fluorine residues from an etching process by a selective etch at a high temperature around 450° C. However, a selective etch at such high temperatures recesses an underlying metal layer undesirably, causing a bottom void in a BEOL process. Chlorine or fluorine residues that are not removed may degrade dielectric layers, which also leads to a short margin concern.

(3) Therefore, there is a need for methods of selectively removing metal oxides, such as molybdenum oxide (MoO.sub.x) and tungsten oxide (WO.sub.x), without damaging an underlying layer and reducing chlorine or fluorine residues.

SUMMARY

(4) Embodiments of the present disclosure provide a method of pre-cleaning in a semiconductor structure. The method includes performing a plasma pre-treatment process to remove impurities from a surface of a semiconductor structure comprising a metal layer and a dielectric layer, performing a selective etch process to remove molybdenum oxide and tungsten oxide from a surface of the metal layer, the selective etch process comprising soaking the semiconductor structure in a precursor including molybdenum chloride (MoCl.sub.5, MoCl.sub.6) at a temperature of between 250° C. and 450° C., and performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure.

(5) Embodiments of the present disclosure provide a method of pre-cleaning in a semiconductor structure. The method includes performing a plasma pre-treatment process to remove impurities from a surface of a semiconductor structure comprising a metal layer and a dielectric layer, performing a selective etch process to remove molybdenum oxide and tungsten oxide from a surface of the metal layer, the selective etch process comprising soaking the semiconductor structure in a precursor including tungsten chloride (WCl.sub.5, WCl.sub.6) at a temperature of between 250° C. and 450° C., and performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure.

(6) Embodiments of the present disclosure provide a method of pre-cleaning in a semiconductor structure. The method includes performing a selective etch process to remove molybdenum oxide and tungsten oxide from a surface of a semiconductor structure comprising a metal layer and a dielectric layer, the selective etch process comprising: soaking the semiconductor structure in a precursor including at least one of molybdenum chloride (MoCl.sub.5, MoCl.sub.6), tungsten chloride (WCl.sub.5, WCl.sub.6), tungsten fluoride (WF.sub.6), and molybdenum fluoride (MoF.sub.6) at a temperature of between 250° C. and 450° C., wherein the metal layer comprises molybdenum (Mo).

Description

BRIEF DESCRIPTION OF THE DRAWINGS

(1) So that the manner in which the above recited features of embodiments of the present disclosure can be understood in detail, a more particular description of the disclosure, briefly summarized above, may be had by reference to embodiments, some of which are illustrated in the appended drawings. It is to be noted, however, that the appended drawings illustrate only typical embodiments of this disclosure and are therefore not to be considered limiting of its scope, for the disclosure may admit to other equally effective embodiments.

- (2) FIG. 1 is a schematic top view of a multi-chamber processing system, according to one or more embodiments of the present disclosure
- (3) FIGS. 2A and 2B are schematic views of an exemplary semiconductor structure.
- (4) FIG. 3 depicts a process flow diagram of a method of metal oxide pre-clean for bottom-up molybdenum (Mo) gap-fill in MEOL and BEOL structures, according to one or more embodiments of the present disclosure.
- (5) FIG. 4A illustrates an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) by a selective etch process using a precursor including molybdenum (V) chloride (MoCl.sub.5).
- (6) FIG. 4B illustrates amount of chlorine residues after a selective etch process.
- (7) To facilitate understanding, identical reference numerals have been used, where possible, to designate identical elements that are common to the figures. It is contemplated that elements disclosed in one embodiment may be beneficially utilized on other embodiments without specific recitation.

DETAILED DESCRIPTION

(8) Embodiments of the present disclosure generally relate to a low temperature selective etch process to selectively remove metal oxides, such as molybdenum oxide and tungsten oxide. At low temperature of between about 250° C. and about 450° C., for example, between about 250° C. and about 350° C., an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) is more than 16 as compared to about 7 in a conventional selective etch process performed at about 450° C. A low temperature selective etch is also effective in reducing chlorine residues at a surface of a dielectric layer.

Processing System Example

- (9) FIG. 1 is a schematic top view of a multi-chamber processing system **100**, according to one or more embodiments of the present disclosure. The processing system **100** generally includes a factory interface **102**, load lock chambers **104**, **106**, transfer chambers **108**, **110** with respective transfer robots **112**, **114**, holding chambers **116**, **118**, and processing chambers **120**, **122**, **124**, **126**, **128**, **130**. As detailed herein, substrates in the processing system **100** can be processed in and transferred between the various chambers without exposing the substrates to an ambient environment exterior to the processing system **100** (e.g., an atmospheric ambient environment such as may be present in a fab). For example, the substrates can be processed in and transferred between the various chambers maintained at a low pressure (e.g., less than or equal to about 300 Torr) or vacuum environment without breaking the low pressure or vacuum environment among various processes performed on the substrates in the processing system **100**. Accordingly, the processing system **100** may provide for an integrated solution for some processing of substrates.
- (10) Examples of a processing system that may be suitably modified in accordance with the teachings provided herein include the Endura®, Producer® or Centura® integrated processing systems or other suitable processing systems commercially available from Applied Materials, Inc., located in Santa Clara, California. It is contemplated that other processing systems (including those from other manufacturers) may be adapted to benefit from aspects described herein.
- (11) In the illustrated example of FIG. 1, the factory interface **102** includes a docking station **132** and factory interface robots **134** to facilitate transfer of substrates. The docking station **132** is adapted to accept one or more front opening unified pods (FOUPs) **136**. In some examples, each factory interface robot **134** generally includes a blade **138** disposed on one end of the respective factory interface robot **134** adapted to transfer the substrates from the factory interface **102** to the load lock chambers **104**, **106**.
- (12) The load lock chambers **104**, **106** have respective ports **140**, **142** coupled to the factory interface **102** and respective ports **144**, **146** coupled to the transfer chamber **108**. The transfer chamber **108** further has respective ports **148**, **150** coupled to the holding chambers **116**, **118** and respective ports **152**, **154** coupled to processing chambers **120**, **122**. Similarly, the transfer chamber **110** has respective ports **156**, **158** coupled to the holding chambers **116**, **118** and respective ports

160, 162, 164, 166 coupled to processing chambers **124, 126, 128, 130**. The ports **144, 146, 148, 150, 152, 154, 156, 158, 160, 162, 164, 166** can be, for example, slit valve openings with slit valves for passing substrates therethrough by the transfer robots **112, 114** and for providing a seal between respective chambers to prevent a gas from passing between the respective chambers. Generally, any port is open for transferring a substrate therethrough. Otherwise, the port is closed.

(13) The load lock chambers **104, 106**, transfer chambers **108, 110**, holding chambers **116, 118**, and processing chambers **120, 122, 124, 126, 128, 130** may be fluidly coupled to a gas and pressure control system (not specifically illustrated). The gas and pressure control system can include one or more gas pumps (e.g., turbo pumps, cryo-pumps, roughing pumps), gas sources, various valves, and conduits fluidly coupled to the various chambers. In operation, a factory interface robot **134** transfers a substrate from a FOUP **136** through a port **140** or **142** to a load lock chamber **104** or **106**. The gas and pressure control system then pumps down the load lock chamber **104** or **106**. The gas and pressure control system further maintains the transfer chambers **108, 110** and holding chambers **116, 118** with an interior low pressure or vacuum environment (which may include an inert gas). Hence, the pumping down of the load lock chamber **104** or **106** facilitates passing the substrate between, for example, the atmospheric environment of the factory interface **102** and the low pressure or vacuum environment of the transfer chamber **108**.

(14) With the substrate in the load lock chamber **104** or **106** that has been pumped down, the transfer robot **112** transfers the substrate from the load lock chamber **104** or **106** into the transfer chamber **108** through the port **144** or **146**. The transfer robot **112** is then capable of transferring the substrate to and/or between any of the processing chambers **120, 122** through the respective ports **152, 154** for processing and the holding chambers **116, 118** through the respective ports **148, 150** for holding to await further transfer. Similarly, the transfer robot **114** is capable of accessing the substrate in the holding chamber **116** or **118** through the port **156** or **158** and is capable of transferring the substrate to and/or between any of the processing chambers **124, 126, 128, 130** through the respective ports **160, 162, 164, 166** for processing and the holding chambers **116, 118** through the respective ports **156, 158** for holding to await further transfer. The transfer and holding of the substrate within and among the various chambers can be in the low pressure or vacuum environment provided by the gas and pressure control system.

(15) The processing chambers **120, 122, 124, 126, 128, 130** can be any appropriate chamber for processing a substrate. In some examples, the processing chamber **120** can be capable of performing an etch process, the processing chamber **122** can be capable of performing a cleaning process, and the processing chambers **126, 128, 130** can be capable of performing respective epitaxial growth processes. The processing chamber **120** may be a Selectra™ Etch chamber available from Applied Materials of Santa Clara, Calif. The processing chamber **122** may be a SiCoNi™ Pre-clean chamber available from Applied Materials of Santa Clara, Calif. The processing chamber **126, 128, or 130** may be a Centura™ Epi chamber, Volta™ CVD/ALD chamber, or Encore™ PVD chambers available from Applied Materials of Santa Clara, Calif.

(16) A system controller **168** is coupled to the processing system **100** for controlling the processing system **100** or components thereof. For example, the system controller **168** may control the operation of the processing system **100** using a direct control of the chambers **104, 106, 108, 110, 116, 118, 120, 122, 124, 126, 128, 130** of the processing system **100** or by controlling controllers associated with the chambers **104, 106, 108, 110, 116, 118, 120, 122, 124, 126, 128, 130**. In operation, the system controller **168** enables data collection and feedback from the respective chambers to coordinate performance of the processing system **100**.

(17) The system controller **168** generally includes a central processing unit (CPU) **170**, memory **172**, and support circuits **174**. The CPU **170** may be one of any form of a general-purpose processor that can be used in an industrial setting. The memory **172**, or non-transitory computer-readable medium, is accessible by the CPU **170** and may be one or more of memory such as random access memory (RAM), read only memory (ROM), floppy disk, hard disk, or any other

form of digital storage, local or remote. The support circuits **174** are coupled to the CPU **170** and may comprise cache, clock circuits, input/output subsystems, power supplies, and the like. The various methods disclosed herein may generally be implemented under the control of the CPU **170** by the CPU **170** executing computer instruction code stored in the memory **172** (or in memory of a particular processing chamber) as, for example, a software routine. When the computer instruction code is executed by the CPU **170**, the CPU **170** controls the chambers to perform processes in accordance with the various methods.

(18) Other processing systems can be in other configurations. For example, more or fewer processing chambers may be coupled to a transfer apparatus. In the illustrated example, the transfer apparatus includes the transfer chambers **108**, **110** and the holding chambers **116**, **118**. In other examples, more or fewer transfer chambers (e.g., one transfer chamber) and/or more or fewer holding chambers (e.g., no holding chambers) may be implemented as a transfer apparatus in a processing system.

Example Semiconductor Structure to Pre-Clean

(19) Fabrication of an integrated circuit may include three stages: front-end-of-line (FEOL), middle-end-of-line (MEOL), and back-end-of-line (BEOL) stages. The MEOL stage may include forming gate regions of the transistors and local interconnect layers proximate to the semiconductor substrate to connect the transistors. The BEOL stage may include forming metal interconnect layers to connect the transistors and other devices of the integrated circuit.

(20) FIGS. 2A and 2B are schematic views of an exemplary semiconductor structure **200**. FIG. 2A illustrates a MEOL portion **200A** of the semiconductor structure. FIG. 2B illustrates a BEOL portion **200B** of the semiconductor structure.

(21) The MEOL portion **200A** may include a first level L.sub.1 that includes a metal layer **202** within a first dielectric layer **204** formed on a substrate **206**, and a second level L.sub.2 that includes an interconnect **208** within a second dielectric layer **210** formed on the first level L.sub.1. In the first level L.sub.1, liners **212** may be formed around the metal layer **202**. The metal layer **202** and the interconnect **208** may be formed of molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN). The first dielectric layer **204** and the second dielectric layer **210** may be each formed of dielectric material such as silicon oxide (SiO.sub.2), silicon nitride (Si.sub.3N.sub.4), or silicon oxynitride (SiON). The liners **212** may be formed of titanium nitride (TiN), tantalum nitride (TaN), or tungsten (W). The substrate **206** may include heavily doped regions **214** and a lightly doped region **216**.

(22) During the fabrication of the second level L.sub.2, the semiconductor structure may be exposed to air or other oxidizing environment, and thus a surface of the metal layer **202** at an interface of the first level L and the second level L.sub.2 may be oxidized. Further, an etching process to form a via **218** within the second dielectric layer **210** to form the interconnect **208** may also leave residues, such as chlorine residues or fluorine residues, at the interface of the first level L.sub.1 and the second level L.sub.2. A surface **202S** of the metal layer **202** within the via **218** at the interface of the first level L.sub.1 and the second level L.sub.2 is therefore pre-cleaned prior to filling the via **218** from a bottom surface of the via **218** (the surface **202S** of the metal layer **202**) to form the interconnect **208**.

(23) The BEOL portion **200B** may include the second level L.sub.2 that includes the interconnect **208** formed within the second dielectric layer **210** and a third level L.sub.3 that includes a metal layer **220** formed within a third dielectric layer **222**. In the third level L.sub.3, barrier layers **224** may be formed around the metal layer **220**, and liners **226** may be formed around the barrier layers **224**. The metal layer **220** may be formed of copper (Cu). The third dielectric layer **222** may be formed dielectric material such as silicon oxide (SiO.sub.2), silicon nitride (Si.sub.3N.sub.4), or silicon oxynitride (SiON). The barrier layers **224** may be formed of titanium (Ti) or tantalum (Ta). The liners **226** may be formed of titanium nitride (TiN), tantalum nitride (TaN), or tungsten (W).

(24) During the fabrication of the third level L.sub.3, the semiconductor structure may be exposed

to air or other oxidizing environment, and thus a surface of the interconnect **208** at an interface of the second level L.sub.2 and the third level L.sub.3 may be oxidized. Further, an etching process to form a trench **228** within the third dielectric layer **222** to form the metal layer **220** may also leave residues, such as chlorine residues or fluorine residues, at the interface of the second level L.sub.2 and the third level L.sub.3. A surface **208S** of the interconnect **208** within the trench **228** at the interface of the second level L.sub.2 and the third level L.sub.3 is therefore pre-cleaned prior to filling the trench **228** from a bottom surface of the trench **228** (the surface **208S** of the interconnect **208**) to form the metal layer **220**.

Pre-Clean

(25) FIG. **3** depicts a process flow diagram of a method **300** of metal oxide pre-clean for bottom-up molybdenum (Mo) gap-fill in MEOL and BEOL structures, according to one or more embodiments of the present disclosure. The method **300** can be used to pre-clean a metal surface such as the surface **202S** of the metal layer **202** (e.g., molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN)) prior to filing the via **218** to form the interconnect **208** (e.g., molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN)) in the MEOL portion **200A** shown in FIG. **2A**, and to pre-clean a metal surface such as the surface **208S** of the interconnect **208** (e.g., molybdenum (Mo)) prior to filling the trench **228** to form the metal layer **220** (e.g., molybdenum (Mo)) in the BEOL portion **200B** shown in FIG. **2B**.

(26) The method **300** begins with block **310**, in which a plasma pre-treatment process is performed to remove impurities from a surface of a metal layer (such as the surface **202S** of the metal layer **202** or the surface **208S** of the interconnect **208**) and a surface of an adjacent dielectric layer (such as a surface **204S** of the first dielectric layer **204** or a surface **210S** of the second dielectric layer **210**) of the semiconductor structure **200**.

(27) In some embodiments, the plasma pre-treatment process includes exposing the surface of the metal layer and the surface of the dielectric layer to a plasma formed from a process gas including both hydrogen (H.sub.2)-containing gas and oxygen (O.sub.2) gas. The plasma pre-treatment process may be an inductively coupled plasma (ICP) process performed in a processing chamber, such as Volta™ chamber available from Applied Materials of Santa Clara, Calif., or a capacitively coupled plasma (CCP) process performed in a processing chamber, such as Preclean XT chamber available from Applied Materials, Inc., of Santa Clara, Calif.

(28) In some embodiments, the plasma pre-treatment process includes exposing the surface of the metal layer and the surface of the dielectric layer to a plasma formed from a process gas including hydrogen (H.sub.2)-containing gas and a plasma formed from a process gas including oxygen (O.sub.2) gas in sequence. The plasma pre-treatment process may be an inductively coupled plasma (ICP) process performed in a processing chamber, such as Volta™ chamber available from Applied Materials of Santa Clara, Calif., a capacitively coupled plasma (CCP) process performed in a processing chamber, such as Preclean XT chamber available from Applied Materials of Santa Clara, Calif., or a remote plasma assisted process performed in a processing chamber, such as Aktiv™ Preclean (APC) chamber available from Applied Materials of Santa Clara, Calif.

(29) In block **320**, a selective etch process is performed to selectively remove metal oxides, such as molybdenum oxide (MoO.sub.x) (x=2 or 3) and tungsten oxide (WO.sub.x), on the pre-treated surface of the metal layer.

(30) The selective etch process to selectively remove metal oxides, such as molybdenum oxide (MoO.sub.x) (x=2 or 3) and tungsten oxide (WO.sub.x), over metals, such as molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN), is performed at a low temperature of between about 250° C. and about 450° C., for example, between about 250° C. and about 350° C., using a precursor including at least one of tungsten chloride (WCl.sub.5, WCl.sub.6), molybdenum chloride (MoCl.sub.5, MoCl.sub.6), tungsten fluoride (WF.sub.6), and molybdenum fluoride (MoF.sub.6). In the selective etch process, a semiconductor structure to be pre-cleaned is soaked in a precursor that is provided in a pulsing flow or a continuous flow in a processing

chamber, such as the processing chamber **124**, **126**, **128**, or **130** shown in FIG. 1.

(31) Due to chemical reactions of metal oxides, such as molybdenum oxide ($\text{MoO}_{x/2}$) and tungsten oxide ($\text{WO}_{x/2}$), with a precursor (e.g., tungsten chloride (WCl_5 , WCl_6), molybdenum chloride (MoCl_5 , MoCl_6), tungsten fluoride (WF_6), molybdenum fluoride (MoF_6)) during the selective etch process, by-products such as $\text{MoCl}_{x/2}$ and $\text{WCl}_{x/2}$ in addition to chlorine residues or fluorine residues remain at the surfaces of the metal layer and the dielectric layer. Byproducts and chlorine or fluorine residues may degrade dielectric layers, which also lead to a short margin concern. In the subsequent step in block **330**, the by-products and the chlorine or fluorine residues are removed.

(32) Conventionally, a pre-clean process to selectively remove metal oxides, such as molybdenum oxide ($\text{MoO}_{x/2}$) ($x=2$ or 3) and tungsten oxide ($\text{WO}_{x/2}$), over metals, such as molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN), is performed at a higher temperature of about 450°C . Damages on dielectric layers and dielectric layers can be repaired. However, the precursor may act as a metal etcher at such high temperatures, recessing underlying metals undesirably. This recess may cause a bottom void in a BEOL process.

(33) The inventors have discovered that an etch selectivity of molybdenum oxide ($\text{MoO}_{x/2}$) to molybdenum (Mo) can be significantly improved by a selective etch process at a lower temperature, and thus recessing of underlying metals can be avoided. For example, as shown in FIG. 4A, an etch selectivity of molybdenum oxide ($\text{MoO}_{x/2}$) to molybdenum (Mo) is 7.2 at 450°C ., and increases to 9.7 at 350°C . and to 16.1 at 250°C ., by a selective etch process using a precursor including molybdenum (V) chloride (MoCl_5). In FIG. 4A, a measured etch amount of molybdenum oxide ($\text{MoO}_{x/2}$) increases significantly as the temperature decreases from 450°C . to 350°C ., and a measured etch amount of molybdenum (Mo) decreases slightly as the temperature decreases from 350°C . to 250°C . The inventors have observed similar increase of etch selectivity of molybdenum oxide ($\text{MoO}_{x/2}$) to molybdenum (Mo) in a selective etch process using a precursor including tungsten (V) chloride (WCl_5).

(34) The inventors have also discovered that chlorine residues at a surface of a dielectric layer can be reduced by a selective etch process at a lower temperature. For example, a surface X-ray photoelectron spectroscopy (XPS) at a dielectric substrate shown in FIG. 4B indicates much less chlorine residues are present after a selective etch process at 250°C . than by a selective etch process at 450°C . This reduction is more significant, for example, to about 20% of a selective etch process at 450°C ., when a pulsing precursor is used, as compared to when a continuous flow (CF) precursor is used.

(35) In block **330**, a post-treatment process is performed to remove chlorine or fluorine residues and by-products (e.g., as $\text{MoCl}_{x/2}$ and $\text{WCl}_{x/2}$) from the selective etch process in block **320** remained at the surfaces of the metal layer and the dielectric layer.

(36) In some embodiments, the post-treatment process includes a plasma post-treatment process in which the surface of the metal layer and the surface of the dielectric layer are exposed to a plasma formed from a process gas including hydrogen (H_2)-containing gas. The plasma post-treatment process may be an inductively coupled plasma (ICP) process performed in a processing chamber, such as Preclean XT chamber available from Applied Materials of Santa Clara, Calif., a capacitively coupled plasma (CCP) process performed in a processing chamber, such as VoltaTM chamber available from Applied Materials of Santa Clara, Calif., a remote plasma assisted process performed in a processing chamber, such as VoltaTM chamber, AktivTM Preclean (APC) chamber, or Preclean XT chamber available from Applied Materials of Santa Clara, Calif., a remote plasma cleaning (RPC) process, or a remote plasma lid (RPL) process. The plasma post-treatment may be a low energy (e.g., less than about 50 eV) plasma treatment to protect the surface of the metal layer and the surface of the dielectric layer.

(37) In some embodiments, the post-treatment process includes a thermal bake process in which the surface of the metal layer and the surface of the dielectric layer are heated to and maintained at a

high temperature of between about 350° C. and about 450° C. while a hydrogen (H.sub.2) containing or a moisture (H.sub.2O) containing gas is flowed onto the surfaces. The thermal bake process may be performed at a high pressure of between about 10 Torr and about 300 Torr.

(38) The remaining chlorine or fluorine residues may be further removed by hydrogen (H.sub.2) based reduction pre-clean, an argon and inert-gas based sputter pre-clean, or a combination thereof.

(39) Therefore, in the embodiments described herein, a pre-clean process to selectively remove metal oxides, such as molybdenum oxide (MoO.sub.x) (x=2 or 3) and tungsten oxide (WO.sub.x), over metals, such as molybdenum (Mo), tungsten (W), tungsten carbide (WC), or tungsten nitride (WN), is performed by a selective etch process at a low temperature of between about 250° C. and about 450° C., for example, between about 250° C. and about 350° C., using a precursor including at least one of molybdenum (V) chloride (MoCl.sub.5), tungsten (V) chloride (WCl.sub.5), tungsten fluoride (WF.sub.6), and molybdenum fluoride (MoF.sub.6).

(40) At this temperature range, molybdenum oxide (MoO.sub.x) and tungsten oxide (WO.sub.x) can be fully removed without damaging an underlying surface. This low temperature soak process can be used to prepare a clean surface **202S** of the metal layer **202** at the interface of the first level L.sub.1 and the second level L.sub.2 prior to filling the via **218** with metal to form the interconnect **208** or a clean surface **208S** of the interconnect **208** at the interface of the second level L.sub.2 and the third level L.sub.3 prior to filling the trench **228** with metal to form the metal layer **220**.

(41) In the embodiments of the present disclosure, a low temperature selective etch process to selectively remove molybdenum oxide and tungsten oxide is provided. At low temperature of between about 250° C. and about 350° C., an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) is more than 16 as compared to about 7 in a conventional selective etch process performed at about 450° C. A low temperature selective etch is also effective in reducing chlorine or fluorine residues at a surface of a dielectric layer.

Claims

1. A method of pre-cleaning in a semiconductor structure, the method comprising: performing a plasma pre-treatment process to remove impurities from a surface of the semiconductor structure comprising a metal layer and a dielectric layer, wherein the plasma pre-treatment process comprises exposing the surface of the semiconductor structure to a plasma formed from a process gas including hydrogen (H.sub.2)-containing gas and a plasma formed from a process gas including oxygen (O.sub.2) gas in sequence; performing a selective etch process to remove molybdenum oxide from a surface of the metal layer, the selective etch process comprising soaking the semiconductor structure in a precursor including at least one of molybdenum chloride (MoCl.sub.5 or MoCl.sub.6) or tungsten chloride (WCl.sub.5 or WCl.sub.6) at a temperature of between 250° C. and 450° C.; and performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure, wherein the post-treatment process comprises a capacitively coupled plasma (CCP) process, in which the surface of the semiconductor structure is exposed to a plasma formed from a hydrogen (H.sub.2)-containing gas.
2. The method of claim 1, wherein an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) is more than 16.
3. The method of claim 1, wherein the plasma pre-treatment process comprises an inductively coupled plasma (ICP) process, a capacitively coupled plasma (CCP) process, or a remote plasma assisted process.
4. A method of pre-cleaning in a semiconductor structure, the method comprising: performing a plasma pre-treatment process to remove impurities from a surface of the semiconductor structure comprising a metal layer and a dielectric layer; performing a selective etch process to remove molybdenum oxide from a surface of the metal layer, the selective etch process comprising soaking

the semiconductor structure in a precursor including at least one of molybdenum chloride (MoCl.sub.5 or MoCl.sub.6) or tungsten chloride (WCl.sub.5 or WCl.sub.6) at a temperature of between 250° C. and 450° C.; and performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure, wherein the post-treatment process comprises a thermal bake process, in which the surface of the semiconductor structure is heated to and maintained at a temperature of between 350° C. and 450° C.

5. The method of claim 4, wherein an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) is more than 16.

6. The method of claim 4, wherein the plasma pre-treatment process comprises exposing the surface of the semiconductor structure to a plasma formed from a process gas including both hydrogen (H.sub.2)-containing gas and oxygen (O.sub.2) gas.

7. The method of claim 5, wherein the plasma pre-treatment process comprises an inductively coupled plasma (ICP) process or a capacitively coupled plasma (CCP) process performed.

8. The method of claim 4, wherein the plasma pre-treatment process comprises exposing the surface of the semiconductor structure to a plasma formed from a process gas including hydrogen (H.sub.2)-containing gas and a plasma formed from a process gas including oxygen (O.sub.2) gas in sequence.

9. The method of claim 8, wherein the plasma pre-treatment process comprises an inductively coupled plasma (ICP) process, a capacitively coupled plasma (CCP) process, or a remote plasma assisted process.

10. A method of pre-cleaning in a semiconductor structure, the method comprising: performing a plasma pre-treatment process to remove impurities from a surface of the semiconductor structure, wherein the plasma pre-treatment process comprises: an inductively coupled plasma (ICP) process, a capacitively coupled plasma (CCP) process, or a remote plasma assisted process, in which the surface of the semiconductor structure is exposed to a plasma formed from a process gas including hydrogen (H.sub.2)-containing gas and a plasma formed from a process gas including oxygen (O.sub.2) gas in sequence; and performing a selective etch process to remove molybdenum oxide from the surface of the semiconductor structure comprising a metal layer and a dielectric layer, the selective etch process comprising: soaking the semiconductor structure in a precursor including at least one of molybdenum chloride (MoCl.sub.5 or MoCl.sub.6), tungsten chloride (WCl.sub.5 or WCl.sub.6), tungsten fluoride (WF.sub.6), or molybdenum fluoride (MoF.sub.6) at a temperature of between 250° C. and 450° C., wherein the metal layer comprises molybdenum (Mo).

11. The method of claim 10, wherein an etch selectivity of molybdenum oxide (MoO.sub.x) to molybdenum (Mo) is more than 16.

12. The method of claim 10, further comprising: performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure, wherein the post-treatment process comprises a plasma process in which the surface of the semiconductor structure is exposed to a plasma formed from a hydrogen (H.sub.2)-containing gas.

13. The method of claim 10, further comprising: performing a post-treatment process to remove chlorine residues and by-products of the selective etch process on the surface of the semiconductor structure, wherein the post-treatment process comprises a thermal bake process in which the surface of the semiconductor structure is heated to and maintained at a temperature of between 350° C. and 450° C.
